MGBR30L50C

# DUAL MOS GATED BARRIER RECTIFIER

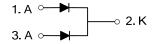
#### DESCRIPTION

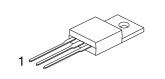
The UTC **MGBR30L50C** is a dual mos g ated barrier rectifiers, it uses UT C's advanc ed tech nology to pro vide custom ers with lo w forward voltage drop and high switching speed, etc.

## **■ FEATURES**

- \* Low forward voltage drop
- \* High switching speed

#### ■ SYMBOL



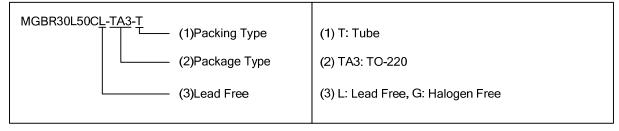


TO-220

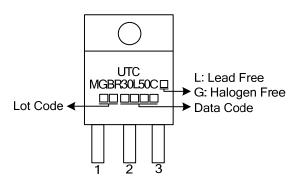
### **■ ORDERING INFORMATION**

Ordering Number		Dookogo	Pin Assignment			Packing	
Lead Free	Halogen Free	Package	1	2	3	Facking	
MGBR30L50CL-TA3-T	MGBR30L50CG-TA3-T	TO-220	Α	Κ	Α	Tube	

Note: Pin Assignment: A: Anode, K: Cathode



### ■ MARKING INFORMATION



www.unisonic.com.tw 1 of 3

MGBR30L50C

# ■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T<sub>A</sub>=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER SYMBOL			RATINGS	UNIT
DC Blocking Voltage		$V_{RM}$ 50		V
Working Peak Reverse Voltage		V <sub>RWM</sub> 50		V
Peak Repetitive Reverse Voltage		$V_{RRM}$ 50		V
Average Restified Output Current Per Device	Per Leg		15 A	
Average Rectified Output Current Per Device	Total 3		0	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I <sub>FSM</sub> 200		Α
Operating Junction Temperature		T <sub>J</sub> -65∼	+150	°C
Storage Temperature		T <sub>STG</sub> -65	+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## **■ THERMAL CHARACTERISTICS (PER LEG)**

PARAMETER SYMBOL		RATINGS	UNIT
Junction to Case	θ <sub>JC</sub> 2		°C/W

## ■ ELECTRICAL CHARACTERISTICS (PER LEG) (T<sub>A</sub> =25°C unless otherwise specified.)

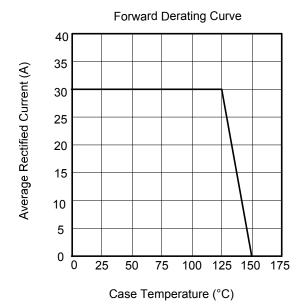
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	V <sub>(BR)R</sub>	I <sub>R</sub> =0.50mA 50				V
Forward Voltage Drop	V <sub>FM</sub>	I <sub>F</sub> =15A, T <sub>J</sub> =25°C			0.60	V
		I <sub>F</sub> =15A, T <sub>J</sub> =125°C			0.55	V
Leakage Current (Note 1)	I PM	V <sub>R</sub> =50V, T <sub>J</sub> =25°C			300	μA
		V <sub>R</sub> =50V, T <sub>J</sub> =125°C			100	mΑ

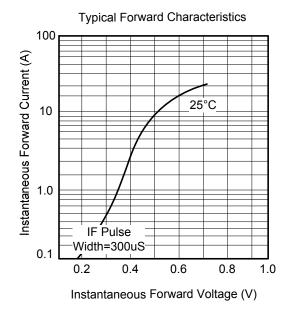
Notes: 1. Short duration pulse test used to minimize self-heating effect.

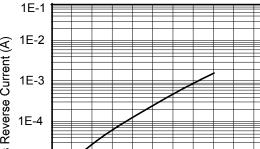
<sup>2.</sup> Thermal resistance junction to case mounted on heatsink.

MGBR30L50C DIODE

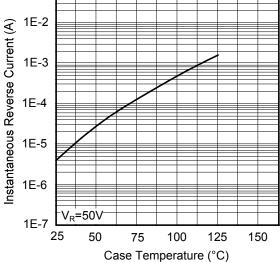
### **TYPICAL CHARACTERISTICS**







Typical Reverse Characteristics



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